

ABSTRACT**METHOD FOR TREATING A STACK OBTAINED DURING THE
MANUFACTURE OF A HETEROJUNCTION PHOTOVOLTAIC CELL**

The invention relates to a method for treating a stack (10') comprising a substrate (11) of n-doped crystalline silicon and a passivation layer (14) of hydrogenated amorphous silicon disposed on a face (11a) of the substrate (11), said method comprising a step of exposing the stack (10') to electromagnetic radiation (20) during a treatment period (t) less than or equal to 12 s, the electromagnetic radiation (20) having an irradiance (E) greater than or equal to 200 kW/m².

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[Figure for the abstract; Figure 2]